

### FEATURES

- 10µs Short Circuit Withstand
- Non Punch Through Silicon
- Isolated Cu Base with Al<sub>2</sub>O<sub>3</sub> Substrates
- Lead Free construction

### APPLICATIONS

- Motor Controllers
- Traction Drives

The Powerline range of high power modules includes half bridge, chopper, dual, single and bi-directional switch configurations covering voltages from 1200V to 6500V and currents up to 2400A.

The DIM1800ESS12-A000 is a single switch 1200V, n-channel enhancement mode, insulated gate bipolar transistor (IGBT) module. The IGBT has a wide reverse bias safe operating area (RBSOA) plus 10µs short circuit withstand. This device is optimised for traction drives and other applications requiring high thermal cycling capability.

The module incorporates an electrically isolated base plate and low inductance construction enabling circuit designers to optimise circuit layouts and utilise grounded heat sinks for safety.

### ORDERING INFORMATION

Order As:

#### DIM1800ESS12-A000

Note: When ordering, please use the complete part number

### KEY PARAMETERS

$V_{CES}$	<b>1200V</b>
$V_{CE(sat)}$ * (typ)	<b>2.2V</b>
$I_C$ (max)	<b>1800A</b>
$I_{C(PK)}$ (max)	<b>3600A</b>

\* Measured at the power busbars, not the auxiliary terminals

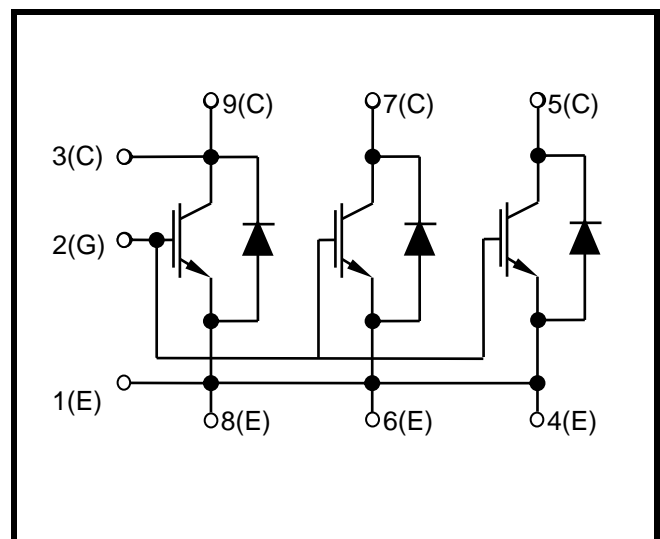


Fig. 1 Circuit configuration



Outline type code: E

(See Fig. 11 for further information)

Fig. 2 Package

## ABSOLUTE MAXIMUM RATINGS

Stresses above those listed under 'Absolute Maximum Ratings' may cause permanent damage to the device. In extreme conditions, as with all semiconductors, this may include potentially hazardous rupture of the package. Appropriate safety precautions should always be followed. Exposure to Absolute Maximum Ratings may affect device reliability.

$T_{case} = 25^{\circ}\text{C}$  unless stated otherwise

Symbol	Parameter	Test Conditions	Max.	Units
$V_{CES}$	Collector-emitter voltage	$V_{GE} = 0\text{V}$	1200	V
$V_{GES}$	Gate-emitter voltage		$\pm 20$	V
$I_C$	Continuous collector current	$T_{case} = 85^{\circ}\text{C}$	1800	A
$I_{C(PK)}$	Peak collector current	1ms, $T_{case} = 115^{\circ}\text{C}$	3600	A
$P_{max}$	Max. transistor power dissipation	$T_{case} = 25^{\circ}\text{C}$ , $T_j = 150^{\circ}\text{C}$	15625	W
$I^2t$	Diode $I^2t$ value	$V_R = 0$ , $t_p = 10\text{ms}$ , $T_j = 125^{\circ}\text{C}$	900	$\text{kA}^2\text{s}$
$V_{isol}$	Isolation voltage – per module	Commoned terminals to base plate. AC RMS, 1 min, 50Hz	2500	V

## THERMAL AND MECHANICAL RATINGS

Internal insulation material:	$\text{Al}_2\text{O}_3$
Baseplate material:	Cu
Creepage distance:	33mm
Clearance:	20mm
CTI (Comparative Tracking Index):	>600

Symbol	Parameter	Test Conditions	Min	Typ.	Max	Units
$R_{th(j-c)}$	Thermal resistance – transistor	Continuous dissipation - junction to case	-	-	8	$^{\circ}\text{C}/\text{kW}$
$R_{th(j-c)}$	Thermal resistance – diode	Continuous dissipation - junction to case	-	-	13	$^{\circ}\text{C}/\text{kW}$
$R_{th(c-h)}$	Thermal resistance – case to heatsink (per module)	Mounting torque 5Nm (with mounting grease)	-	-	6	$^{\circ}\text{C}/\text{kW}$
$T_j$	Junction temperature	Transistor	-	-	150	$^{\circ}\text{C}$
		Diode	-	-	125	$^{\circ}\text{C}$
$T_{stg}$	Storage temperature range	-	-40	-	125	$^{\circ}\text{C}$
	Screw torque	Mounting – M6	-	-	5	Nm
		Electrical connections – M4	-	-	2	Nm
		Electrical connections – M8	-	-	10	Nm

**ELECTRICAL CHARACTERISTICS**
**T<sub>case</sub> = 25°C unless stated otherwise.**

Symbol	Parameter	Test Conditions	Min	Typ	Max	Units
I <sub>CES</sub>	Collector cut-off current	V <sub>GE</sub> = 0V, V <sub>CE</sub> = V <sub>CES</sub>			3	mA
		V <sub>GE</sub> = 0V, V <sub>CE</sub> = V <sub>CES</sub> , T <sub>case</sub> = 125°C			75	mA
I <sub>GES</sub>	Gate leakage current	V <sub>GE</sub> = ± 20V, V <sub>CE</sub> = 0V			12	μA
V <sub>GE(TH)</sub>	Gate threshold voltage	I <sub>C</sub> = 90mA, V <sub>GE</sub> = V <sub>CE</sub>	4.5	5.5	6.5	V
V <sub>CE(sat)</sub>	Collector-emitter saturation voltage	V <sub>GE</sub> = 15V, I <sub>C</sub> = 1800A		2.2	2.8	V
		V <sub>GE</sub> = 15V, I <sub>C</sub> = 1800A, T <sub>j</sub> = 125°C		2.6	3.3	V
I <sub>F</sub>	Diode forward current	DC			1800	A
I <sub>FM</sub>	Diode maximum forward current	t <sub>p</sub> = 1ms			3600	A
V <sub>F</sub>	Diode forward voltage	I <sub>F</sub> = 1800A		1.9	2.1	V
		I <sub>F</sub> = 1800A, T <sub>j</sub> = 125°C		1.8	2.1	V
C <sub>ies</sub>	Input capacitance	V <sub>CE</sub> = 25V, V <sub>GE</sub> = 0V, f = 1MHz		200		nF
Q <sub>g</sub>	Gate charge	±15V		20		μC
C <sub>res</sub>	Reverse transfer capacitance	V <sub>CE</sub> = 25V, V <sub>GE</sub> = 0V, f = 1MHz				nF
L <sub>M</sub>	Module inductance			10		nH
R <sub>INT</sub>	Internal transistor resistance			90		μΩ
SC <sub>Data</sub>	Short circuit current, I <sub>SC</sub>	T <sub>j</sub> = 125°C, V <sub>CC</sub> = 900V t <sub>p</sub> ≤ 10μs, V <sub>GE</sub> ≤ 15V V <sub>CE(max)</sub> = V <sub>CES</sub> - L* x di/dt IEC 60747-9		10000		A

**Note:**

 \* L is the circuit inductance + L<sub>M</sub>

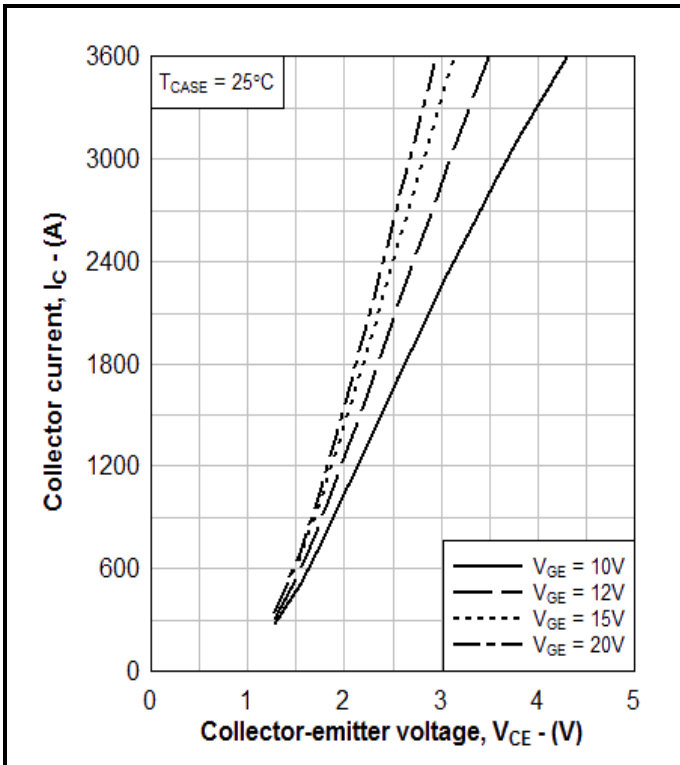
## ELECTRICAL CHARACTERISTICS

$T_{\text{case}} = 25^{\circ}\text{C}$  unless stated otherwise

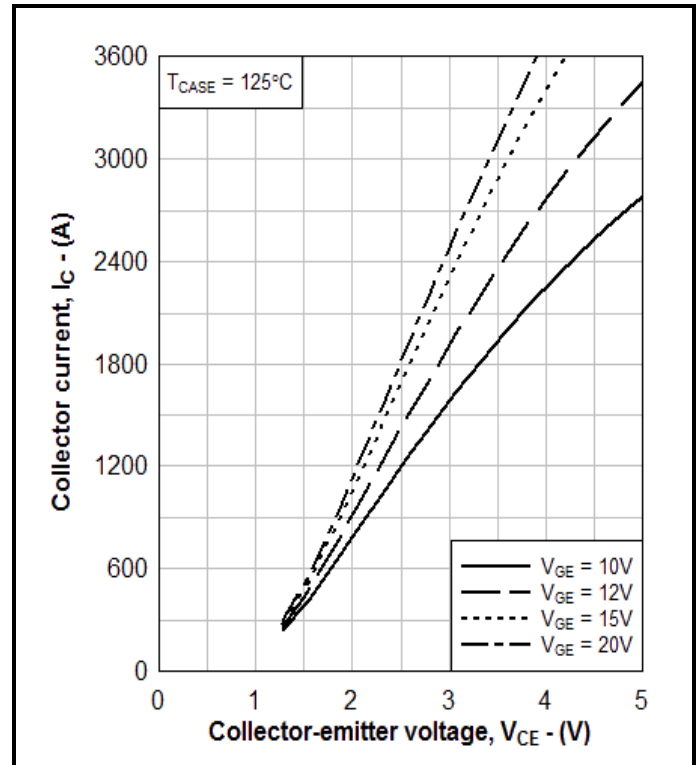
Symbol	Parameter	Test Conditions	Min	Typ.	Max	Units
$t_{d(\text{off})}$	Turn-off delay time	$I_C = 1800\text{A}$ $V_{GE} = \pm 15\text{V}$ $V_{CE} = 600\text{V}$ $R_{G(\text{ON})} = 1.2\Omega$ $R_{G(\text{OFF})} = 1.2\Omega$ $L_S \sim 60\text{nH}$		1250		ns
$t_f$	Fall time			190		ns
$E_{\text{OFF}}$	Turn-off energy loss			330		mJ
$t_{d(\text{on})}$	Turn-on delay time			220		ns
$t_r$	Rise time			200		ns
$E_{\text{ON}}$	Turn-on energy loss			100		mJ
$Q_{rr}$	Diode reverse recovery charge		$I_F = 1800\text{A}$ $V_{CE} = 600\text{V}$ $di_F/dt = 9000\text{A}/\mu\text{s}$		210	
$I_{rr}$	Diode reverse recovery current			860		A
$E_{rec}$	Diode reverse recovery energy			110		mJ

$T_{\text{case}} = 125^{\circ}\text{C}$  unless stated otherwise

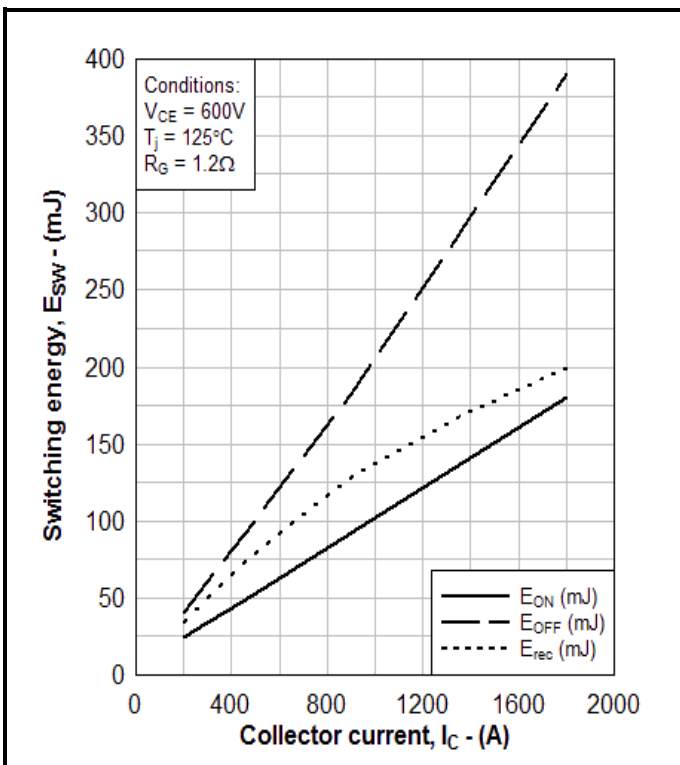
Symbol	Parameter	Test Conditions	Min	Typ.	Max	Units
$t_{d(\text{off})}$	Turn-off delay time	$I_C = 1200\text{A}$ $V_{GE} = \pm 15\text{V}$ $V_{CE} = 600\text{V}$ $R_{G(\text{ON})} = 1.2\Omega$ $R_{G(\text{OFF})} = 1.2\Omega$ $L_S \sim 60\text{nH}$		1450		ns
$t_f$	Fall time			190		ns
$E_{\text{OFF}}$	Turn-off energy loss			390		mJ
$t_{d(\text{on})}$	Turn-on delay time			230		ns
$t_r$	Rise time			340		ns
$E_{\text{ON}}$	Turn-on energy loss			180		mJ
$Q_{rr}$	Diode reverse recovery charge		$I_F = 1800\text{A}$ $V_{CE} = 600\text{V}$ $di_F/dt = 8000\text{A}/\mu\text{s}$		390	
$I_{rr}$	Diode reverse recovery current			1100		A
$E_{rec}$	Diode reverse recovery energy			200		mJ



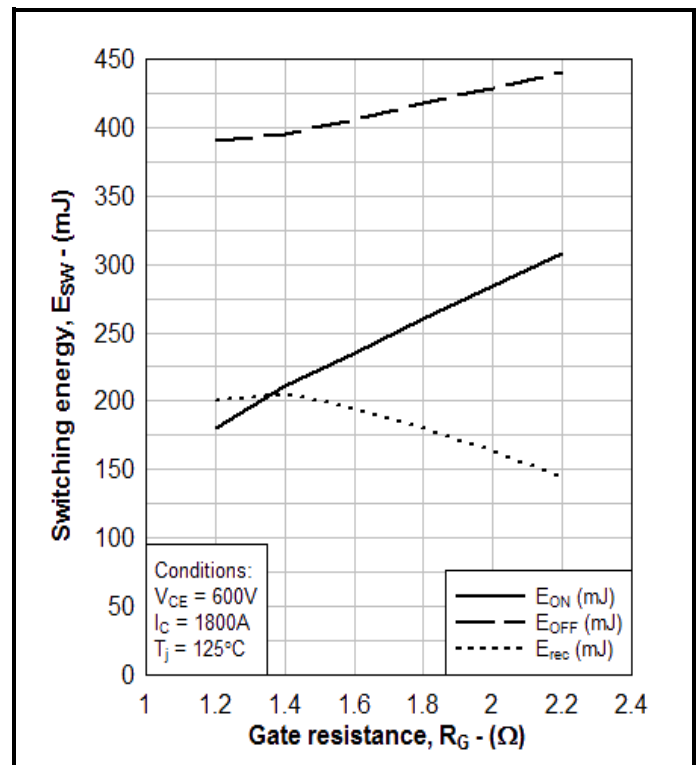
**Fig. 3 Typical output characteristics**



**Fig. 4 Typical output characteristics**



**Fig. 5 Typical switching energy vs collector current**



**Fig. 6 Typical switching energy vs gate resistance**

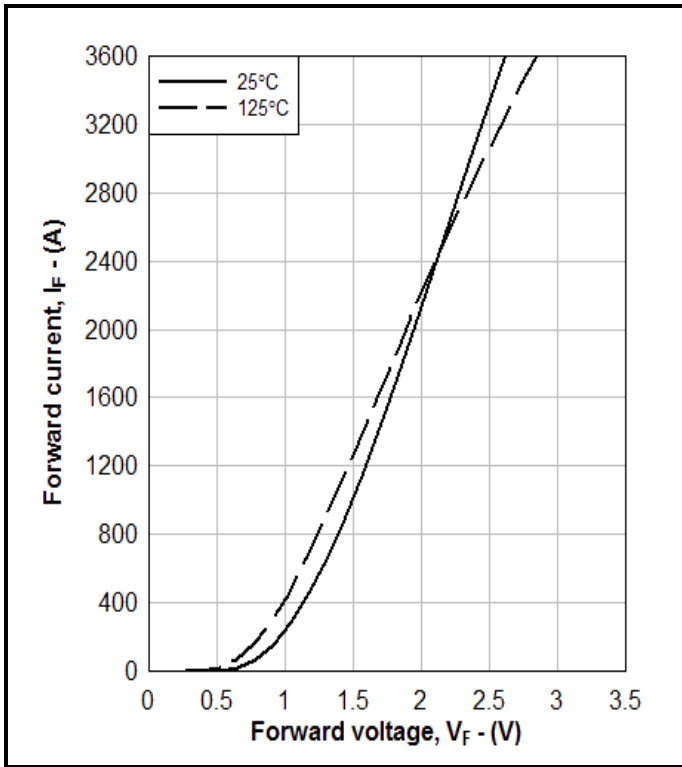


Fig. 7 Diode typical forward characteristics

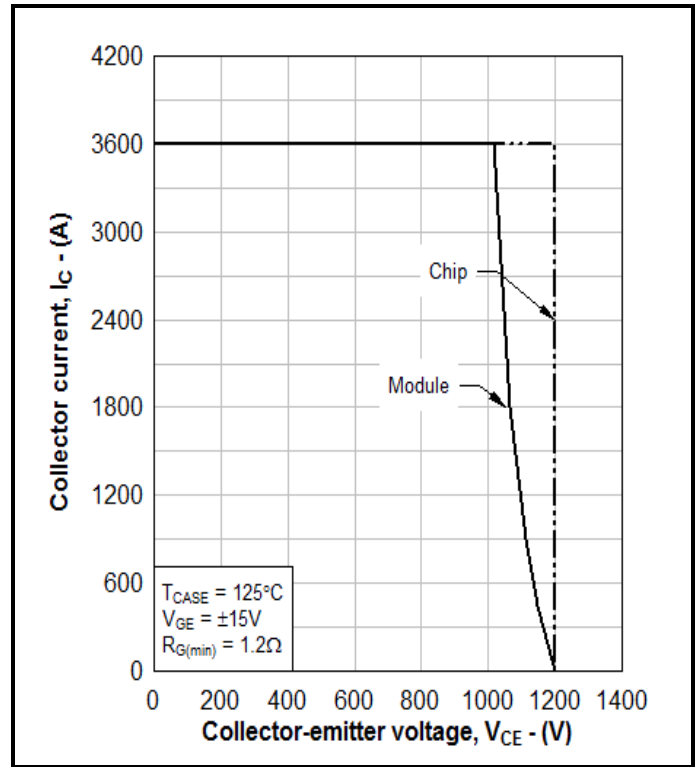


Fig. 8 Reverse bias safe operating area

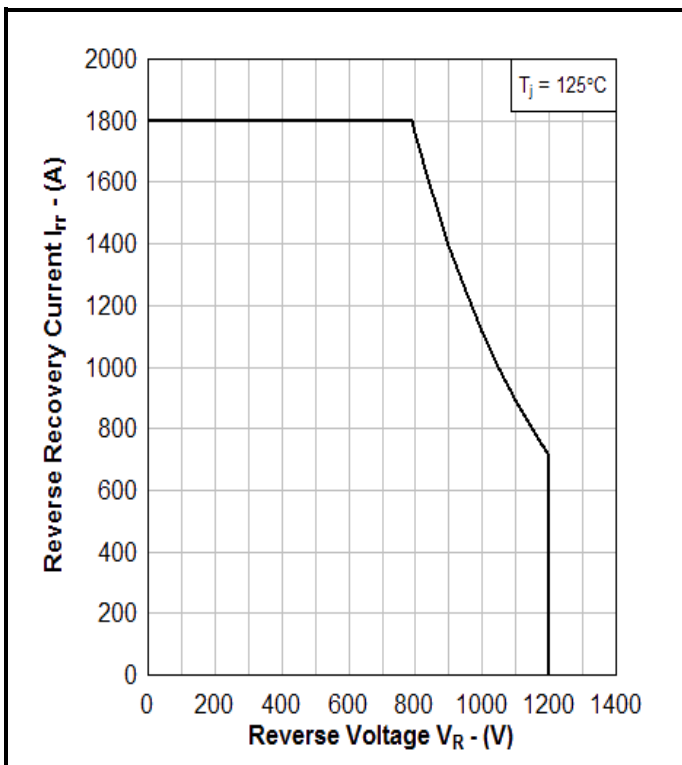


Fig. 9 Diode reverse bias safe operating area

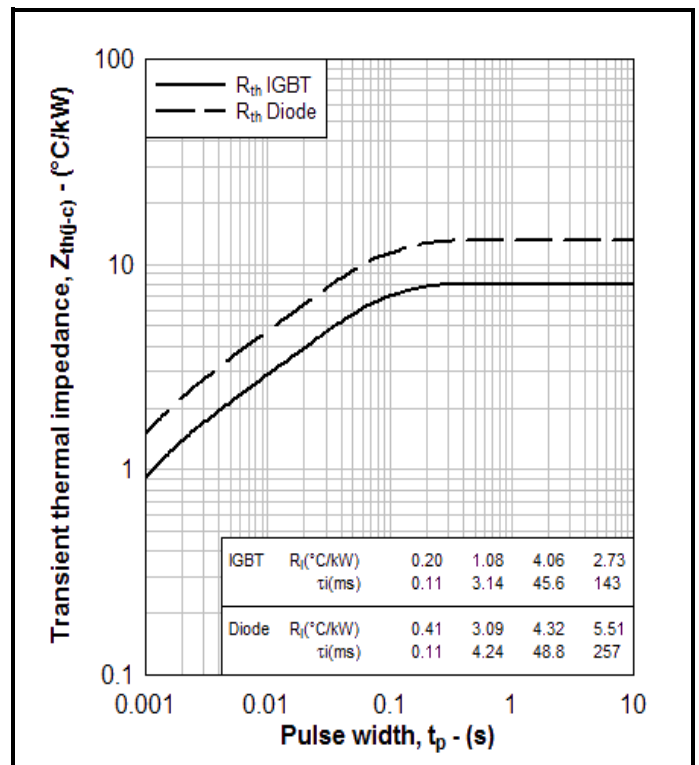


Fig. 10 Transient thermal impedance



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